Dual Buffer with Open Drain Outputs

NL27WZ07

The NL27WZ07 is a high performance dual buffer with open drain outputs operating from a 1.65 to 5.5 V supply.

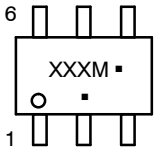
Features

- Designed for 1.65 V to 5.5 V V_{CC} Operation
- 2.1 ns t_{PD} at V_{CC} = 5 V (Typ)
- Inputs/Outputs Overvoltage Tolerant up to 5.5 V
- I_{OFF} Supports Partial Power Down Protection
- Sink 24 mA at 3.0 V
- Available in SC-88, SC-74 and UDFN6 Packages
- Chip Complexity < 100 FETs
- −Q Suffix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

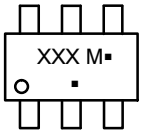
Figure 1. Logic Symbol

MARKING DIAGRAMS

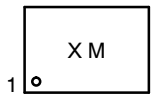
SC-88
DF SUFFIX
CASE 419B



SC-74
CASE318F-05



UDFN6
1.45 x 1.0 x 0.5P
CASE 517AQ



X, XXX = Specific Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 7 of this data sheet.

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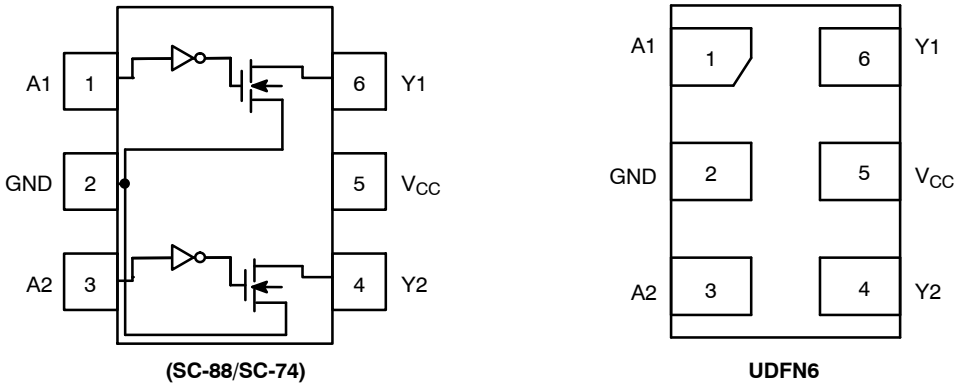

Figure 2. Pinout (Top View)

PIN ASSIGNMENT

Pin	Function
1	A1
2	GND
3	A2
4	Y2
5	V_{CC}
6	Y1

FUNCTION TABLE

A Input	Y Output
L	L
H	Z

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MAXIMUM RATINGS

Symbol	Characteristics		Value	Unit
V_{CC}	DC Supply Voltage		−0.5 to +6.5	V
V_{IN}	DC Input Voltage		−0.5 to +6.5	V
V_{OUT}	DC Output Voltage	Active-Mode (High or Low State) Tri-State Mode (Note 1) Power-Down Mode (V_{CC} = 0 V)	−0.5 to V_{CC} + 0.5 −0.5 to +6.5 −0.5 to +6.5	V
I_{IK}	DC Input Diode Current	V_{IN} < GND	−50	mA
I_{OK}	DC Output Diode Current	V_{OUT} < GND	−50	mA
I_{OUT}	DC Output Source/Sink Current		±50	mA
I_{CC} or I_{GND}	DC Supply Current per Supply Pin or Ground Pin		±100	mA
T_{STG}	Storage Temperature Range		−65 to +150	°C
T_L	Lead Temperature, 1 mm from Case for 10 secs		260	°C
T_J	Junction Temperature Under Bias		+150	°C
θ_{JA}	Thermal Resistance (Note 2)	SC-88 SC-74 UDFN6	377 320 154	°C/W
P_D	Power Dissipation in Still Air	SC-88 SC-74 UDFN6	332 390 812	mW
MSL	Moisture Sensitivity		Level 1	
F_R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	
V_{ESD}	ESD Withstand Voltage (Note 3)	Human Body Model Charged Device Model	2000 1000	V
$I_{Latchup}$	Latchup Performance (Note 4)		± 100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Applicable to devices with outputs that may be tri-stated.
2. Measured with minimum pad spacing on an FR4 board, using 10mm-by-1inch, 2 ounce copper trace no air flow per JESD51-7.
3. HBM tested to ANSI/ESDA/JEDEC JS-001-2017. CDM tested to EIA/JESD22-C101-F. JEDEC recommends that ESD qualification to EIA/JESD22-A115-A (Machine Model) be discontinued per JEDEC/JEP172A.
4. Tested to EIA/JESD78 Class II.

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RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics		Min	Max	Unit
V_{CC}	Positive DC Supply Voltage		1.65	5.5	V
V_{IN}	DC Input Voltage		0	5.5	V
V_{OUT}	DC Output Voltage	Active-Mode (High or Low State) Tri-State Mode (Note 1) Power-Down Mode (V_{CC} = 0 V)	0 0 0	V_{CC} 5.5 5.5	
T_A	Operating Temperature Range		−55	+125	°C
t_r , t_f	Input Rise and Fall Time	V_{CC} = 1.65 V to 1.95 V V_{CC} = 2.3 V to 2.7 V V_{CC} = 3.0 V to 3.6 V V_{CC} = 4.5 V to 5.5 V	0 0 0 0	20 20 10 5	ns

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Condition	V_{CC} (V)	T_A = 25 °C			−55 °C ≤ T_A ≤ 125 °C		Units
				Min	Typ	Max	Min	Max	
V_{IH}	High-Level Input Voltage		1.65 to 1.95	0.65 V_{CC}			0.65 V_{CC}		V
			2.3 to 5.5	0.70 V_{CC}			0.70 V_{CC}		
V_{IL}	Low-Level Input Voltage		1.65 to 1.95			0.35 V_{CC}		0.35 V_{CC}	V
			2.3 to 5.5			0.30 V_{CC}		0.30 V_{CC}	
V_{OL}	Low-Level Output Voltage	V_{IN} = V_{IH} or V_{IL} I_{OL} = 100 μA I_{OL} = 4 mA I_{OL} = 8 mA I_{OL} = 12 mA I_{OL} = 16 mA I_{OL} = 24 mA I_{OL} = 32 mA	 1.65 to 5.5 1.65 2.3 2.7 3.0 3.0 4.5		 0.08 0.2 0.22 0.28 0.38 0.42	 0.1 0.24 0.3 0.4 0.4 0.55 0.55		 0.1 0.24 0.3 0.4 0.4 0.55 0.55	V
I_{IN}	Input Leakage Current	V_{IN} = 5.5 V or GND	1.65 to 5.5			±0.1		±1.0	μA
I_{OZ}	3-State Output Leakage Current	V_{OUT} = 0 V to 5.5 V	1.65 to 5.5			±0.5		±5.0	μA
I_{OFF}	Power Off Leakage Current	V_{IN} = 5.5 V or V_{OUT} = 5.5 V	0			1.0		10	μA
I_{CC}	Quiescent Supply Current	V_{IN} = V_{CC} or GND	5.5			1.0		10	μA
I_{CCT}	Quiescent Supply Current	V_{IN} = 3.0 V	3.6			10		100	μA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

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AC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Condition	V_{CC} (V)	T_A = 25 °C			−55 °C ≤ T_A ≤ 125 °C		Units
				Min	Typ	Max	Min	Max	
t_{PZL}	Propagation Delay, A to Y (Figures 3 and 4)		1.65 to 1.95		6.0	9.0		9.5	ns
			2.3 to 2.7		3.6	6.1		6.5	
			3.0 to 3.6		2.7	5.6		6.0	
			4.5 to 5.5		2.1	4.4		4.8	
t_{PLZ}	Propagation Delay, A to Y (Figures 3 and 4)		1.65 to 1.95		4.0	9.0		9.5	ns
			2.3 to 2.7		2.8	6.1		6.5	
			3.0 to 3.6		2.5	5.6		6.0	
			4.5 to 5.5		2.2	4.4		4.8	

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Units
C_{IN}	Input Capacitance	V_{CC} = 5.5 V, V_{IN} = 0 V or V_{CC}	2.5	pF
C_{OUT}	Output Capacitance	V_{CC} = 5.5 V, V_{IN} = 0 V or V_{CC}	4.0	pF
C_{PD}	Power Dissipation Capacitance (Note 5)	10 MHz, V_{CC} = 5.5 V, V_{IN} = 0 V or V_{CC}	4.0	pF

5. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$. C_{PD} is used to determine the no-load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.

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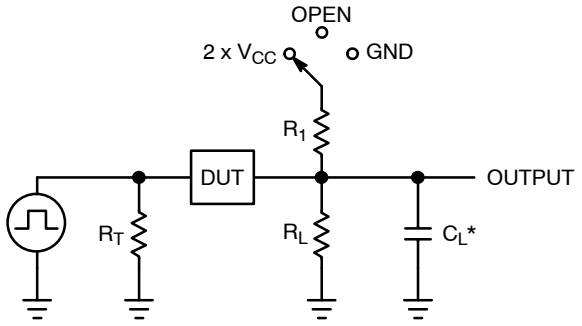

C_L includes probe and jig capacitance
R_T is Z_{OUT} of pulse generator (typically 50 Ω)
f = 1 MHz

Figure 3. Test Circuit

Test	Switch Position	C_L, pF	R_L, Ω	R_1, Ω
t_{PLH} / t_{PHL}	Open	See AC Characteristics Table		
t_{PLZ} / t_{PZL}	2 x V_{CC}	50	500	500
t_{PHZ} / t_{PZH}	GND	50	500	500

X = Don't Care

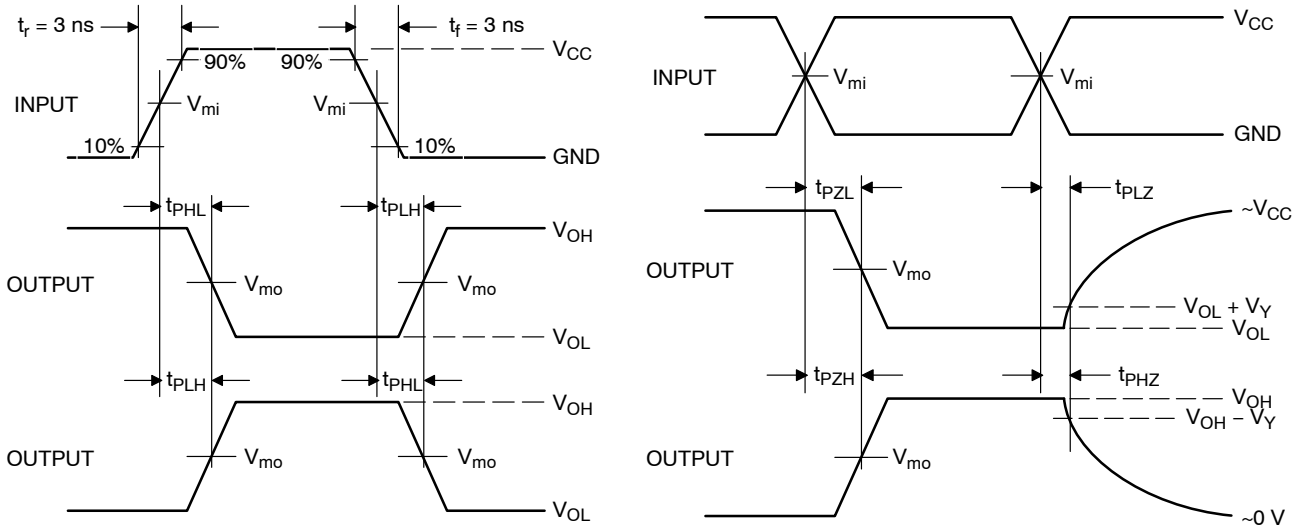

Figure 4. Switching Waveforms

V_{CC}, V	V_{mi}, V	V_{mo}, V		V_Y, V
		t_{PLH}, t_{PHL}	t_{PZL}, t_{PLZ}, t_{PZH}, t_{PHZ}	
1.65 to 1.95	V_{CC}/2	V_{CC}/2	V_{CC}/2	0.15
2.3 to 2.7	V_{CC}/2	V_{CC}/2	V_{CC}/2	0.15
3.0 to 3.6	V_{CC}/2	V_{CC}/2	V_{CC}/2	0.3
4.5 to 5.5	V_{CC}/2	V_{CC}/2	V_{CC}/2	0.3

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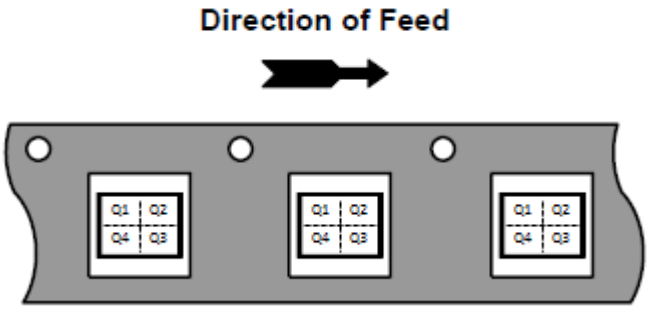
DEVICE ORDERING INFORMATION

Device	Packages	Specific Device Code	Pin 1 Orientation (See below)	Shipping†
NL27WZ07DFT2G	SC-88	M7	Q4	3000 / Tape & Reel
NL27WZ07DFT2G-Q*	SC-88	M7	Q4	3000 / Tape & Reel
NL27WZ07DBVT1G	SC-74	M7	Q4	3000 / Tape & Reel
NL27WZ07MU1TCG	UDFN6, 1.45 x 1.0 x 0.5P	V (Rotated 90° CW)	Q4	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*–Q Suffix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

PIN 1 ORIENTATION IN TAPE AND REEL



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REVISION HISTORY

Revision	Description of Changes	Date
19	Remove two package options and related OPNs	2/2/2026

This document has undergone updates prior to the inclusion of this revision history table. The changes tracked here only reflect updates made on the noted approval dates.

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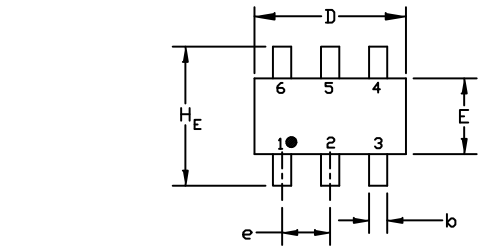
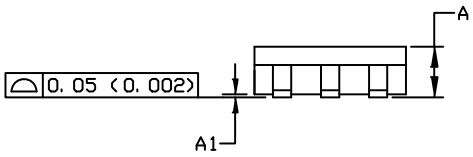
SCALE 2:1

SC−74
CASE 318F
ISSUE P

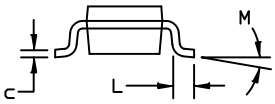
DATE 07 OCT 2021



TOP VIEW



SIDE VIEW

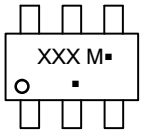


END VIEW

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994
2. CONTROLLING DIMENSION: INCHES
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.

	MILLIMETERS			INCHES		
DIM	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.90	1.00	1.10	0.035	0.039	0.043
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.25	0.37	0.50	0.010	0.015	0.020
c	0.10	0.18	0.26	0.004	0.007	0.010
D	2.90	3.00	3.10	0.114	0.118	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
e	0.85	0.95	1.05	0.034	0.037	0.041
H_E	2.50	2.75	3.00	0.099	0.108	0.118
L	0.20	0.40	0.60	0.008	0.016	0.024
M	0°	---	10°	0°	---	10°

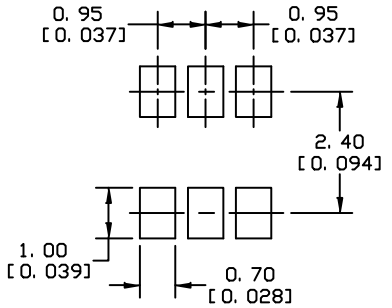
GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.



* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

SOLDERING FOOTPRINT

STYLE 1:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. ANODE
6. CATHODE

STYLE 2:
PIN 1. NO CONNECTION
2. COLLECTOR
3. EMITTER
4. NO CONNECTION
5. COLLECTOR
6. BASE

STYLE 3:
PIN 1. EMITTER 1
2. BASE 1
3. COLLECTOR 2
4. EMITTER 2
5. BASE 2
6. COLLECTOR 1

STYLE 4:
PIN 1. COLLECTOR 2
2. EMITTER 1/EMITTER 2
3. COLLECTOR 1
4. EMITTER 3
5. BASE 1/BASE 2/COLLECTOR 3
6. BASE 3

STYLE 5:
PIN 1. CHANNEL 1
2. ANODE
3. CHANNEL 2
4. CHANNEL 3
5. CATHODE
6. CHANNEL 4

STYLE 6:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. CATHODE
6. CATHODE

STYLE 7:
PIN 1. SOURCE 1
2. GATE 1
3. DRAIN 2
4. SOURCE 2
5. GATE 2
6. DRAIN 1

STYLE 8:
PIN 1. EMITTER 1
2. BASE 2
3. COLLECTOR 2
4. EMITTER 2
5. BASE 1
6. COLLECTOR 1

STYLE 9:
PIN 1. EMITTER 2
2. BASE 2
3. COLLECTOR 1
4. EMITTER 1
5. BASE 1
6. COLLECTOR 2

STYLE 10:
PIN 1. ANODE/CATHODE
2. BASE
3. EMITTER
4. COLLECTOR
5. ANODE
6. CATHODE

STYLE 11:
PIN 1. EMITTER
2. BASE
3. ANODE/CATHODE
4. ANODE
5. CATHODE
6. COLLECTOR

DOCUMENT NUMBER:	**98ASB42973B**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.
DESCRIPTION:	**SC−74**	**PAGE 1 OF 1**

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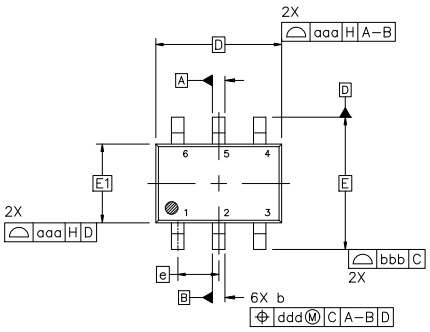
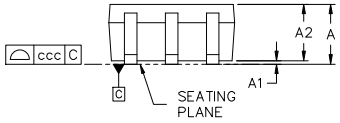
SC−88 2.00x1.25x0.90, 0.65P
CASE 419B−02
ISSUE Z

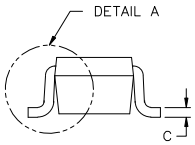
DATE 18 APR 2024



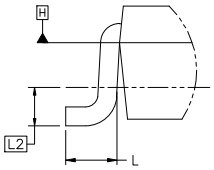
TOP VIEW



SIDE VIEW



END VIEW

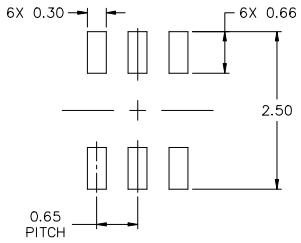


DETAIL A
SCALE 2:1

NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5−2018.
2. ALL DIMENSION ARE IN MILLIMETERS.
3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
5. DATUMS A AND B ARE DETERMINED AT DATUM H.
6. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
7. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

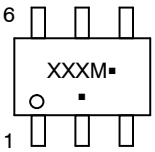
	MILLIMETERS		
DIM	MIN.	NOM.	MAX.
A	−−−	−−−	1.10
A1	0.00	−−−	0.10
A2	0.70	0.90	1.00
b	0.15	0.20	0.25
c	0.08	0.15	0.22
D	2.00 BSC		
E	2.10 BSC		
E1	1.25 BSC		
e	0.65 BSC		
L	0.26	0.36	0.46
L2	0.15 BSC		
aaa	0.15		
bbb	0.30		
ccc	0.10		
ddd	0.10		



RECOMMENDED MOUNTING FOOTPRINT*

* FOR ADDITIONAL INFORMATION ON OUR Pb−FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



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(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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SC−88 2.00x1.25x0.90, 0.65P
CASE 419B−02
ISSUE Z

DATE 18 APR 2024

STYLE 1:
PIN 1. EMITTER 2
2. BASE 2
3. COLLECTOR 1
4. EMITTER 1
5. BASE 1
6. COLLECTOR 2

STYLE 2:
CANCELLED

STYLE 3:
CANCELLED

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. COLLECTOR
4. EMITTER
5. BASE
6. ANODE

STYLE 5:
PIN 1. ANODE
2. ANODE
3. COLLECTOR
4. EMITTER
5. BASE
6. CATHODE

STYLE 6:
PIN 1. ANODE 2
2. N/C
3. CATHODE 1
4. ANODE 1
5. N/C
6. CATHODE 2

STYLE 7:
PIN 1. SOURCE 2
2. DRAIN 2
3. GATE 1
4. SOURCE 1
5. DRAIN 1
6. GATE 2

STYLE 8:
CANCELLED

STYLE 9:
PIN 1. EMITTER 2
2. EMITTER 1
3. COLLECTOR 1
4. BASE 1
5. BASE 2
6. COLLECTOR 2

STYLE 10:
PIN 1. SOURCE 2
2. SOURCE 1
3. GATE 1
4. DRAIN 1
5. DRAIN 2
6. GATE 2

STYLE 11:
PIN 1. CATHODE 2
2. CATHODE 2
3. ANODE 1
4. CATHODE 1
5. CATHODE 1
6. ANODE 2

STYLE 12:
PIN 1. ANODE 2
2. ANODE 2
3. CATHODE 1
4. ANODE 1
5. ANODE 1
6. CATHODE 2

STYLE 13:
PIN 1. ANODE
2. N/C
3. COLLECTOR
4. EMITTER
5. BASE
6. CATHODE

STYLE 14:
PIN 1. VREF
2. GND
3. GND
4. IOUT
5. VEN
6. VCC

STYLE 15:
PIN 1. ANODE 1
2. ANODE 2
3. ANODE 3
4. CATHODE 3
5. CATHODE 2
6. CATHODE 1

STYLE 16:
PIN 1. BASE 1
2. EMITTER 2
3. COLLECTOR 2
4. BASE 2
5. EMITTER 1
6. COLLECTOR 1

STYLE 17:
PIN 1. BASE 1
2. EMITTER 1
3. COLLECTOR 2
4. BASE 2
5. EMITTER 2
6. COLLECTOR 1

STYLE 18:
PIN 1. VIN1
2. VCC
3. VOUT2
4. VIN2
5. GND
6. VOUT1

STYLE 19:
PIN 1. I OUT
2. GND
3. GND
4. V CC
5. V EN
6. V REF

STYLE 20:
PIN 1. COLLECTOR
2. COLLECTOR
3. BASE
4. EMITTER
5. COLLECTOR
6. COLLECTOR

STYLE 21:
PIN 1. ANODE 1
2. N/C
3. ANODE 2
4. CATHODE 2
5. N/C
6. CATHODE 1

STYLE 22:
PIN 1. D1 (i)
2. GND
3. D2 (i)
4. D2 (c)
5. VBUS
6. D1 (c)

STYLE 23:
PIN 1. Vn
2. CH1
3. Vp
4. N/C
5. CH2
6. N/C

STYLE 24:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. CATHODE
6. CATHODE

STYLE 25:
PIN 1. BASE 1
2. CATHODE
3. COLLECTOR 2
4. BASE 2
5. EMITTER
6. COLLECTOR 1

STYLE 26:
PIN 1. SOURCE 1
2. GATE 1
3. DRAIN 2
4. SOURCE 2
5. GATE 2
6. DRAIN 1

STYLE 27:
PIN 1. BASE 2
2. BASE 1
3. COLLECTOR 1
4. EMITTER 1
5. EMITTER 2
6. COLLECTOR 2

STYLE 28:
PIN 1. DRAIN
2. DRAIN
3. GATE
4. SOURCE
5. DRAIN
6. DRAIN

STYLE 29:
PIN 1. ANODE
2. ANODE
3. COLLECTOR
4. EMITTER
5. BASE/ANODE
6. CATHODE

STYLE 30:
PIN 1. SOURCE 1
2. DRAIN 2
3. DRAIN 2
4. SOURCE 2
5. GATE 1
6. DRAIN 1

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

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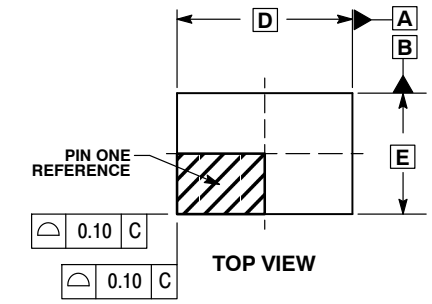
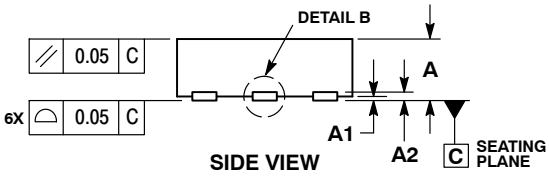
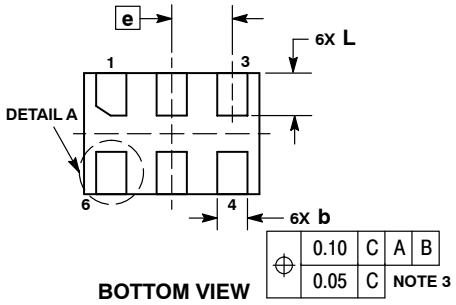
SCALE 4:1

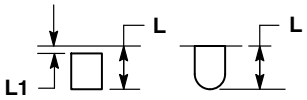
UDFN6, 1.45x1.0, 0.5P
CASE 517AQ
ISSUE O

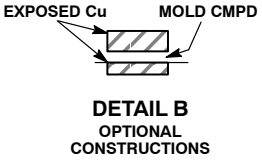
DATE 15 MAY 2008







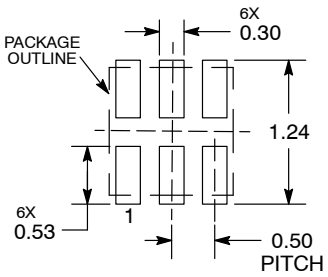




NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 mm FROM THE TERMINAL TIP.

	MILLIMETERS	
DIM	MIN	MAX
A	0.45	0.55
A1	0.00	0.05
A2	0.07 REF	
b	0.20	0.30
D	1.45 BSC	
E	1.00 BSC	
e	0.50 BSC	
L	0.30	0.40
L1	---	0.15

MOUNTING FOOTPRINT



DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*

X = Specific Device Code
M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present.

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